<u>Standard specifications of</u> 100 mm Sn-doped β-Ga₂O₃ (001) substrate

Items		Specifications	
Orientation		(001)	
Dopant		Sn	
Conductivity		n-type	
Resistivity (Ω·cm)		0.007-0.042	
	Diameter (mm)	100 ± 0.5	
Dimensions	Orientation flat width (mm)	32.5 ±2.5	
	Index flat width (mm)	18.0 ±2.5	
	Thickness (mm)	0.65 ± 0.02	
	Reference	Fig. 1	
Offset angle (degree)		[010]:0 ±1	
		[100]:0 ±1	
FWHM (arcsec)		[010]:50 or less	
		[100]:50 or less	
Surface	Front	СМР	
	Back	СМР	

Remarks

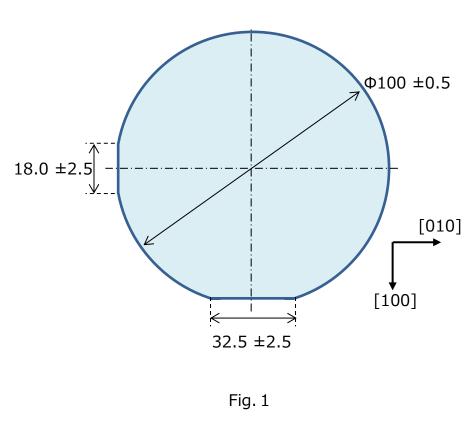
 $1\ \mbox{There}$ are cases in which the opposite side of OF is chipped less than $18\ \mbox{mm}.$

2 There are cases in which the OF side is chipped less than 32.5 mm ± 2.5 mm.

3 These products must be used for research and development purposes only.

4 The substrates must not be used as a seed crystal.

5 The specifications are subject to change without notice.





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<u>Standard specifications of</u> <u>2 inch Sn-doped β-Ga₂O₃ (001) substrate</u>

Items		Specifications	
Orientation		(001)	
Dopant		Sn	
Conductivity		n-type	
Resistivity (Ω·cm)		0.007-0.042	
	Diameter (mm)	50.8 ±0.3	
Dimensions	Orientation flat width (mm)	15.9 ±2.5	
	Index flat width (mm)	8.0 ±2.5	
	Thickness (mm)	0.65 ± 0.02	
	Reference	Fig. 2	
Offset angle (degree)		[010]:0 ±1	
		$[100]:0 \pm 1$	
FWHM (arcsec)		[010]:50 or less	
		[100]:50 or less	
Surface	Front	СМР	
	Back	СМР	

Remarks

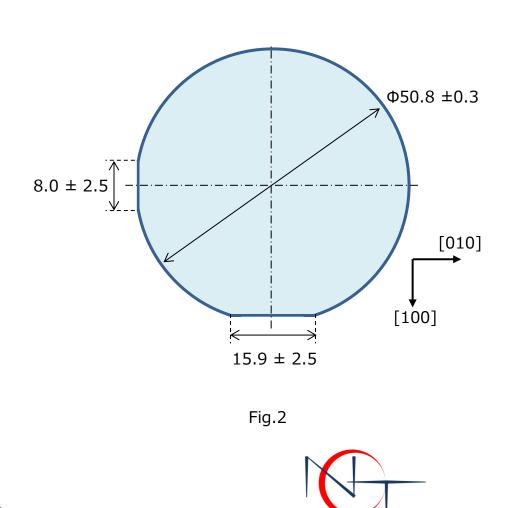
 $1\ \mbox{There}\ \mbox{are}\ \mbox{cases}\ \mbox{in which the opposite side of OF}\ \mbox{is chipped less than }8\ \mbox{mm}.$

2 There are cases in which the OF side is chipped less than 15.9 mm ± 2.5 mm.

3 These products must be used for research and development purposes only.

4 The substrates must not be used as a seed crystal.

5 The specifications are subject to change without notice.

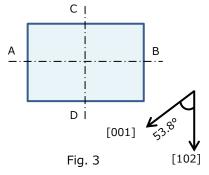


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Standard specifications of 10×15 mm² β-Ga₂O₃ (010) substrates

Items		Specifications			
Orientation		(010)			
Dopant		Sn	Undoped	Fe	
Conductivity		n-type	n-type	Insulating $(> 10^{10}\Omega \cdot cm)$	
Nd-Na (cm ⁻³)		$1 \times 10^{18} - 9 \times 10^{18}$	≦9×10 ¹⁷	-	
Dimensions	A-B (mm)	15 ±0.3	15 ±0.3	15 ±0.3	
	C-D (mm)	10 ±0.3	10 ±0.3	10 ±0.3	
	Thickness (mm)	0.5 ± 0.02	0.5 ± 0.02	0.5 ±0.02	
	Reference	Fig. 3	Fig. 3	Fig. 3	
Offset angle (degree)		⊥[102]:0 ±1	⊥[102]:0 ±1	⊥[102]:0 ±1	
		[102]:0 ±1	[102]:0 ±1	[102]:0 ±1	
FWHM (arcsec)		⊥[102]:150 or less	⊥[102]:150 or less	⊥[102]:150 or less	
		[102]:150 or less	[102]:150 or less	[102]:150 or less	
Surface	Front	СМР	СМР	СМР	
ace	Back	Grinding	Grinding	Grinding	



Remarks

1 These products must be used for research and development purposes only.

2 The substrates must not be used as a seed crystal.

3 The specifications are subject to change without notice.

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